

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	159	"low k" and ("hard mask" or SiN or "silicon nitride" or SiC) and (oxide or dielectric or insulating) and ("CF.sub.4" or "CHF.sub.3") and ("C.sub.4F.sub.8" or "C.sub.4F.sub.6")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:37
L2	759	("hard mask" or SiN or "silicon nitride" or SiC) and (oxide or dielectric or insulating) and ("CF. sub.4" or "CHF.sub.3") and ("C. sub.4F.sub.8" or "C.sub.4F.sub.6")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:02
L3	8643	(dual adj damascene)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:38
L4	195	3 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 10:38
L7	101	("hard mask" or SiN or "silicon nitride" or SiC) same (oxide or dielectric or insulating) same ("CF. sub.4" or "carbon tetrafluoride" or "CHF.sub.3" or trifluoromethane) same ("C.sub.4F.sub.8" or "C.sub.4F.sub.6")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:06
L8	163	("hard mask" or SiN or "silicon nitride" or SiC) and (oxide or dielectric or insulating) and ("CF. sub.4" or "carbon tetrafluoride" or "CHF.sub.3" or trifluoromethane) and ("C.sub.4F.sub.8" or "C.sub.4F.sub.6") and (ARC or BARC or "bottom antireflective coating")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:09
L9	2	kim-jisoo.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:10

L10	1	worsham-binet.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:10
L11	9	yen-bi-ming.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:11
L12	2	"20030190807"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/20 11:11